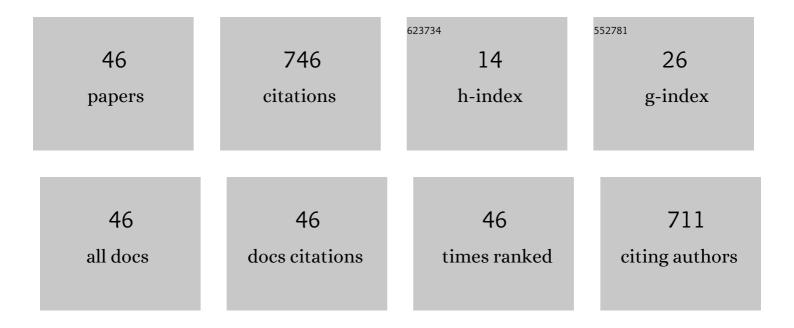
Zinovi Dashevsky

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Thermoelectric efficiency in graded indium-doped PbTe crystals. Journal of Applied Physics, 2002, 92, 1425-1430.	2.5	90
2	Highly textured Bi2Te3-based materials for thermoelectric energy conversion. Journal of Applied Physics, 2007, 101, 113707.	2.5	89
3	The search for mechanically stable PbTe based thermoelectric materials. Journal of Applied Physics, 2008, 104, .	2.5	65
4	Highly efficient bismuth telluride doped pâ€ŧype Pb _{0.13} Ge _{0.87} Te for thermoelectric applications. Physica Status Solidi - Rapid Research Letters, 2007, 1, 232-234.	2.4	57
5	Thermoelectric Properties of (Pb,Sn,Ge)Te-Based Alloys. Journal of Electronic Materials, 2009, 38, 1478-1482.	2.2	54
6	Feasibility of a high stable PbTe:In semiconductor for thermoelectric energy applications. Journal of Applied Physics, 2019, 125, .	2.5	42
7	Highly efficient n-type PbTe developed by advanced electronic structure engineering. Journal of Materials Chemistry C, 2020, 8, 13270-13285.	5.5	36
8	Carrier concentration gradient generated in p-type PbTe crystals by unidirectional solidification. Journal of Crystal Growth, 2002, 234, 164-170.	1.5	31
9	Development of a solid-state multi-stage thermoelectric cooler. Journal of Power Sources, 2021, 496, 229821.	7.8	31
10	High thermoelectric performance of p-type Bi0.5Sb1.5Te3 films on flexible substrate. Materials Chemistry and Physics, 2020, 253, 123427.	4.0	30
11	Thermoelectric, Structural, and Mechanical Properties of Spark-Plasma-Sintered Submicro- and Microstructured p-Type Bi0.5Sb1.5Te3. Journal of Electronic Materials, 2012, 41, 1546-1553.	2.2	29
12	Highly efficient bismuth telluride–based thermoelectric microconverters. Materials Today Energy, 2021, 21, 100753.	4.7	26
13	Infrared detectors based on semiconductor <i>p-n</i> junction of PbSe. Journal of Applied Physics, 2012, 112, .	2.5	25
14	Development of the high performance thermoelectric unicouple based on Bi2Te3 compounds. Journal of Power Sources, 2022, 530, 231301.	7.8	18
15	High-temperature PbTe diodes. Thin Solid Films, 2008, 516, 7065-7069.	1.8	10
16	Minority carrier transport in p-ZnO nanowires. Journal of Applied Physics, 2011, 109, 016107.	2.5	10
17	Development of cryogenic cooler based on n-type Bi-Sb thermoelectric and HTSC. Cryogenics, 2020, 112, 103197.	1.7	10
18	Characterization of high-temperature PbTe p-n junctions prepared by thermal diffusion and by ion implantation. Journal of Applied Physics, 2008, 103, 024506.	2.5	9

ΖΙΝΟΥΙ DASHEVSKY

#	Article	IF	CITATIONS
19	Development of a High Perfomance Gas Thermoelectric Generator (TEG) with Possibible Use of Waste Heat. Energies, 2022, 15, 3960.	3.1	9
20	Transport properties and photo- conductivity of nanocrystalline PbTe(In) films. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, NA-NA.	0.8	8
21	Impact of electron injection on carrier transport and recombination in unintentionally doped GaN. Journal of Applied Physics, 2020, 128, .	2.5	7
22	The Effect of A Graded in Profile on the Figure of Merit of PbTe. Materials Research Society Symposia Proceedings, 1998, 545, 513.	0.1	6
23	Synthesis of n-type PbTe by powder metallurgy. , 0, , .		6
24	Charge transport in photosensitive nanocrystalline PbTe(In) films in an alternating electric field. International Journal of Materials Research, 2009, 100, 1252-1254.	0.3	6
25	Feasibility of high performance in p â€ŧype Ge 1â^' x Bi x Te materials for thermoelectric modules. Journal of the American Ceramic Society, 0, , .	3.8	6
26	Peculiarities of High Power Infrared Detection on Narrow-Gap Semiconductor p-n Junctions. Acta Physica Polonica A, 2011, 119, 237-240.	0.5	5
27	Design, synthesis and characterization of graded n-type PbTe. , 0, , .		4
28	Pyroelectric Effect Induced by the Built-In Field of thepâ^'nJunction in the Quantum Paraelectric PbTe: Experimental Study. Physical Review Letters, 2008, 100, 057603.	7.8	4
29	Improved materials for thermoelectric conversion (generation). , 0, , .		3
30	High efficiency thermoelectric unit within an autonomous solar energy converter. , 0, , .		3
31	The Development of Infrared Photosensitive Material Based on Polycrystalline PbS Films. Materials Research Society Symposia Proceedings, 1999, 607, 353.	0.1	3
32	Photothermal effect in narrow band gap PbTe semiconductor. Journal of Applied Physics, 2009, 106, 076105.	2.5	3
33	Influence of Deformation on Pb 1â^' x In x Te 1â^' y I y and Pb 1â^' x â^' y Sn x In y. Physica Status Solidi (B): Basic Research, 2020, 257, 2000304.	1.5	3
34	Generation of 30 kbar hydrostatic pressure in Bi2Te3 thin films by uniaxial deformation and its effect on the band structure. Physical Review B, 2021, 104, .	3.2	3
35	Optimization of thermoelectric efficiency in graded materials. , 0, , .		2
36	Ultrafast response and high sensitivity semiconductor thermocouple. , 0, , .		1

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ΖΙΝΟΥΙ DASHEVSKY

#	Article	IF	CITATIONS
37	A possibility to realize a high thermoelectric figure of merit in quasi-one-dimensional organic crystals. , 0, , .		1
38	Development of p-Pb1-xSnxTe Functionally Graded Materials. , 2006, , .		1
39	Growth of PbTe films by magnetron sputtering. Materials Research Society Symposia Proceedings, 2001, 691, 1.	0.1	0
40	Characterization of Sputter Deposited PbTe on Si (111) for Optoelectronic Applications. Materials Research Society Symposia Proceedings, 2002, 744, 1.	0.1	0
41	Transport properties of Pbl/sub 2/-doped PbTe. , 0, , .		0
42	Thermoelectric properties of p-type PbTe/PbEuTe quantum well structures. , 0, , .		0
43	Thermoelectric Properties of p-type In-doped Pb1-xSnxTe. , 2006, , .		0
44	Development of thin film thermoelectric sensors for a wide spectral range in the MEMS configuration. , 2006, , .		0
45	Impact of forward bias injection on minority carrier transport in p-type ZnO nanowires. Journal of Applied Physics, 2011, 110, .	2.5	Ο
46	A Novel Method to Significantly Improve the Mechanical Properties of n-Type Bi(1â^'x)Sbx Thermoelectrics Due to Plastic Deformation. Electronic Materials, 2021, 2, 511-526.	1.9	0